



## SOT-23 Plastic-Encapsulate Diodes

### BAW56LT1

SWITCHING DIODE

#### FEATURES

Power dissipation

$P_D$ : 225 mW ( $T_{amb}=25^\circ\text{C}$ )

Forward Current

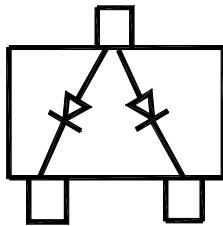
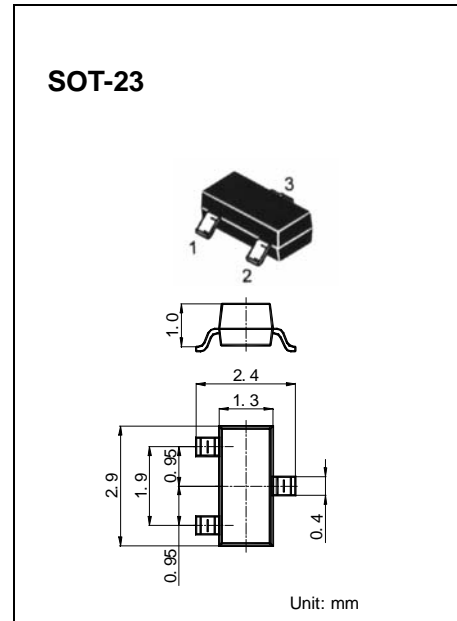
$I_F$ : 200 mA

Reverse Voltage

$V_R$ : 70 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^\circ\text{C}$  to  $+150^\circ\text{C}$



Marking A1

#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	70		V
Reverse voltage leakage current	$I_R$	$V_R=70\text{V}$		2.5	$\mu\text{A}$
Forward voltage	$V_F$	$I_F=1\text{mA}$ $I_F=10\text{mA}$ $I_F=50\text{mA}$ $I_F=150\text{mA}$		715 855 1000 1250	mV
Diode capacitance	$C_D$	$V_R=0\text{V}, f=1\text{MHz}$		2	pF
Reverse recovery time	$t_{rr}$			6	nS